**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020M-6 (SOT1220-2) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- · Logic-level compatible
- Ultra low Q<sub>G</sub>, Q<sub>GD</sub> for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery
- · Low spiking and ringing for low EMI designs
- Exposed drain pad for excellent thermal conduction
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm

## 3. Applications

- DC to DC conversion
- · Battery management
- · Low-side load switch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions   |     | Min | Тур | Max | Unit |
|-------------------|----------------------------------|--|-----|-----|-----|-----|------|
| V <sub>DS</sub>   | drain-source voltage             | T <sub>j</sub> = 25 °C   |     | -   | -   | 30  | V    |
| V <sub>GS</sub>   | gate-source voltage              |  |     | -20 | -   | 20  | V    |
| I <sub>D</sub>    | drain current                    | $V_{GS} = 10 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$    | [1] | -   | -   | 17  | Α    |
| Static characte   | Static characteristics           |  |     |     |     |     |      |
| R <sub>DSon</sub> | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 12 \text{ A}; T_j = 25 ^{\circ}\text{C}$ |     | -   | 7.3 | 8.6 | mΩ   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

### **Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline     | Graphic symbol |
|-----|--------|-------------|------------------------|----------------|
| 1   | D      | drain       | 15/50/6                | D              |
| 2   | D      | drain       | 7                      |                |
| 3   | G      | gate        | 2   5                  | G—(F)          |
| 4   | S      | source      | 3 8 4                  | mbb076 S       |
| 5   | D      | drain       | Transparent top view   |                |
| 6   | D      | drain       | DFN2020M-6 (SOT1220-2) |                |
| 7   | D      | drain       |                        |                |
| 8   | S      | source      |                        |                |

## 6. Ordering information

## **Table 3. Ordering information**

| Type number Package |      |  |           |  |  |  |
|---------------------|------|--|-----------|--|--|--|
|                     | Name | Description  | Version   |  |  |  |
| PMPB07R3EN          |      | plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm | SOT1220-2 |  |  |  |

## 7. Marking

## **Table 4. Marking codes**

| Type number | Marking code |
|-------------|--------------|
| PMPB07R3EN  | ZQ           |

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## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions  |     | Min | Max  | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| $V_{DS}$         | drain-source voltage    | T <sub>j</sub> = 25 °C                                    |     | -   | 30   | V    |
| $V_{GS}$         | gate-source voltage     |   |     | -20 | 20   | V    |
| I <sub>D</sub>   | drain current           | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s | [1] | -   | 17   | А    |
|                  |                         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C          | [1] | -   | 12   | А    |
|                  |                         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C         | [1] | -   | 7.5  | А    |
| I <sub>DM</sub>  | peak drain current      | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$       |     | -   | 48   | Α    |
| P <sub>tot</sub> | total power dissipation | T <sub>amb</sub> = 25 °C; t ≤ 5 s                         | [1] | -   | 3.8  | W    |
|                  |                         | T <sub>amb</sub> = 25 °C                                  | [1] | -   | 1.9  | W    |
|                  |                         | T <sub>sp</sub> = 25 °C                                   |     | -   | 12.5 | W    |
| Tj               | junction temperature    |   |     | -55 | 150  | °C   |
| T <sub>amb</sub> | ambient temperature     |   |     | -55 | 150  | °C   |
| T <sub>stg</sub> | storage temperature     |   |     | -65 | 150  | °C   |
| Source-drain     | n diode                 |   | '   | '   | ·    |      |
| I <sub>S</sub>   | source current          | T <sub>amb</sub> = 25 °C                                  | [1] | -   | 1.9  | А    |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

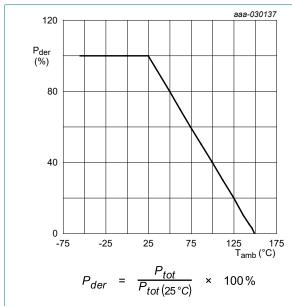


Fig. 1. Normalized total power dissipation as a function of ambient temperature

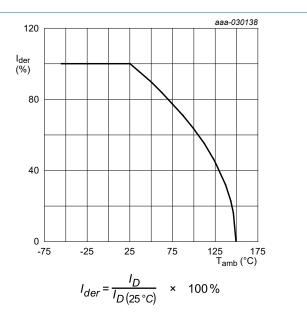


Fig. 2. Normalized continous drain current as a function of ambient temperature

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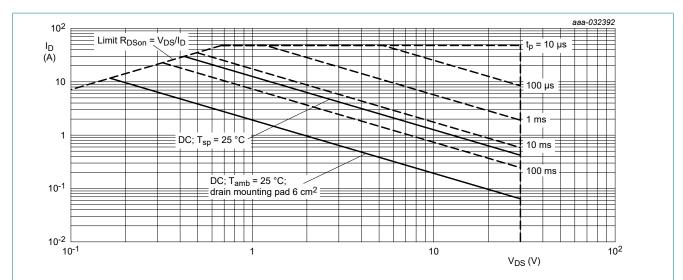


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

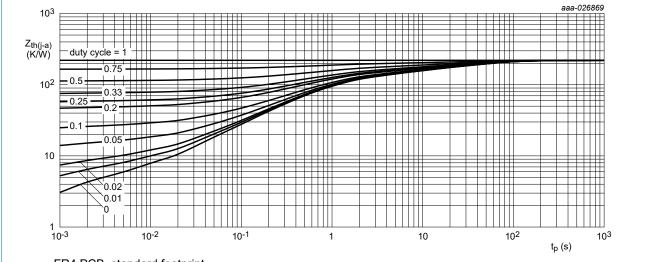
30 V, N-channel Trench MOSFET

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol   | Parameter  | Conditions           |     | Min | Тур | Max | Unit |
|--|--|----------------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub> thermal resistant junction to ambie | thermal resistance from                          | in free air          | [1] | -   | 223 | 256 | K/W  |
|  | junction to ambient                              |                      | [2] | -   | 57  | 66  | K/W  |
|  |  | in free air; t ≤ 5 s | [2] | -   | 29  | 33  | K/W  |
| R <sub>th(j-sp)</sub>                                    | thermal resistance from junction to solder point |                      |     | -   | 6   | 10  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

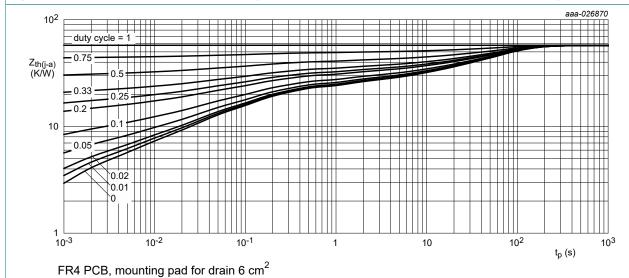


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### **Table 7. Characteristics**

| Symbol               | Parameter                         | Conditions   | Min | Тур | Max  | Unit |
|----------------------|-----------------------------------|--|-----|-----|------|------|
| Static chara         | acteristics                       |  |     |     |      |      |
| V <sub>(BR)DSS</sub> | drain-source<br>breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$                             | 30  | -   | -    | V    |
| $V_{GSth}$           | gate-source threshold voltage     | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$                  | 1.2 | 1.7 | 2.2  | V    |
| I <sub>DSS</sub>     | drain leakage current             | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | -   | -   | 1    | μΑ   |
| I <sub>GSS</sub>     | gate leakage current              | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -   | -   | 100  | nA   |
|                      |                                   | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -   | -   | -100 | nA   |
| DOON                 | drain-source on-state             | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 12 A; T <sub>j</sub> = 25 °C    | -   | 7.3 | 8.6  | mΩ   |
|                      | resistance                        | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 12 A; T <sub>j</sub> = 150 °C   | -   | 12  | 14   | mΩ   |
|                      |                                   | $V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C}$  | -   | 9   | 12   | mΩ   |
| 9fs                  | forward transconductance          | $V_{DS} = 5 \text{ V}; I_D = 12 \text{ A}; T_j = 25 \text{ °C}$          | -   | 2.8 | -    | S    |
| R <sub>G</sub>       | gate resistance                   | f = 1 MHz  | -   | 2.5 | -    | Ω    |
| Dynamic ch           | aracteristics                     |  |     |     |      |      |
| Q <sub>G(tot)</sub>  | total gate charge                 | V <sub>DS</sub> = 15 V; I <sub>D</sub> = 12 A; V <sub>GS</sub> = 10 V;   | -   | 13  | 19   | nC   |
| Q <sub>GS</sub>      | gate-source charge                | T <sub>j</sub> = 25 °C   | -   | 2.3 | -    | nC   |
| Q <sub>GD</sub>      | gate-drain charge                 |  | -   | 1.6 | -    | nC   |
| C <sub>iss</sub>     | input capacitance                 | V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                | -   | 914 | -    | pF   |
| C <sub>oss</sub>     | output capacitance                | T <sub>j</sub> = 25 °C   | -   | 309 | -    | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance      |  | -   | 52  | -    | pF   |
| t <sub>d(on)</sub>   | turn-on delay time                | V <sub>DS</sub> = 15 V; I <sub>D</sub> = 12 A; V <sub>GS</sub> = 10 V;   | -   | 3   | -    | ns   |
| t <sub>r</sub>       | rise time                         | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$                                     | -   | 2   | -    | ns   |
| t <sub>d(off)</sub>  | turn-off delay time               | 1  | -   | 13  | -    | ns   |
| t <sub>f</sub>       | fall time                         | 1  | -   | 3   | -    | ns   |
| Source-drai          | in diode                          |  |     |     |      |      |
| $V_{SD}$             | source-drain voltage              | I <sub>S</sub> = 1.9 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C    | -   | 0.7 | 1.2  | V    |

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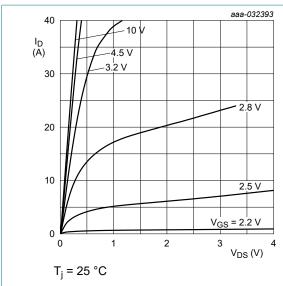


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

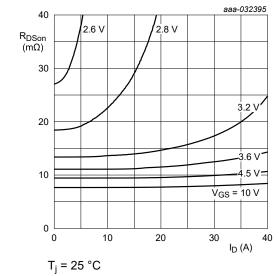
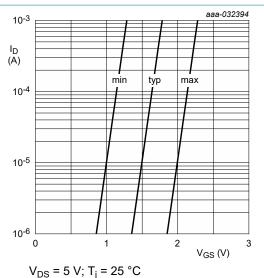


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



 $V_{DS} = 5 \text{ V}; I_{j} = 25 \text{ C}$ 

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

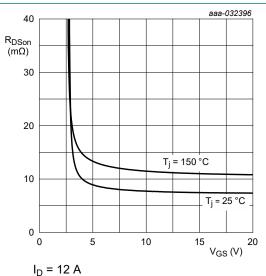


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 30 V, N-channel Trench MOSFET

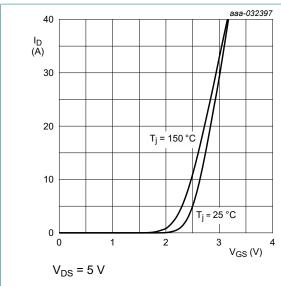


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

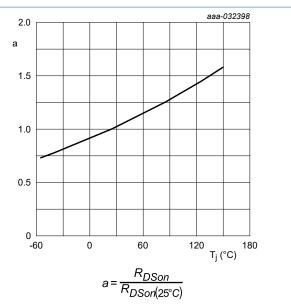


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

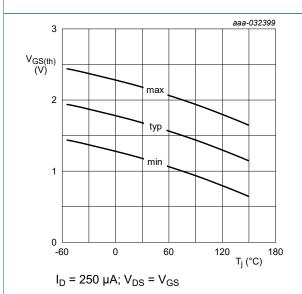


Fig. 12. Gate-source threshold voltage as a function of junction temperature

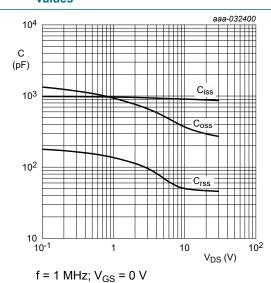


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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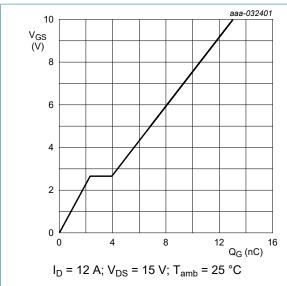


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$ 

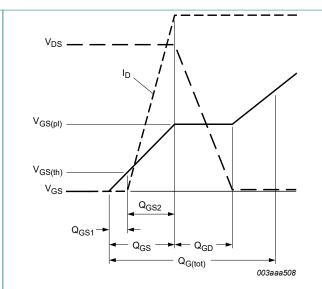


Fig. 15. Gate charge waveform definitions

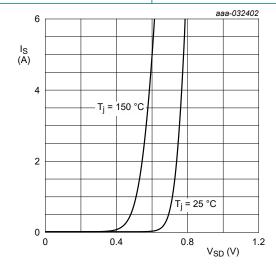
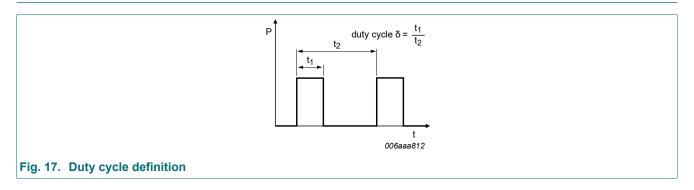


Fig. 16. Source current as a function of source-drain voltage; typical values

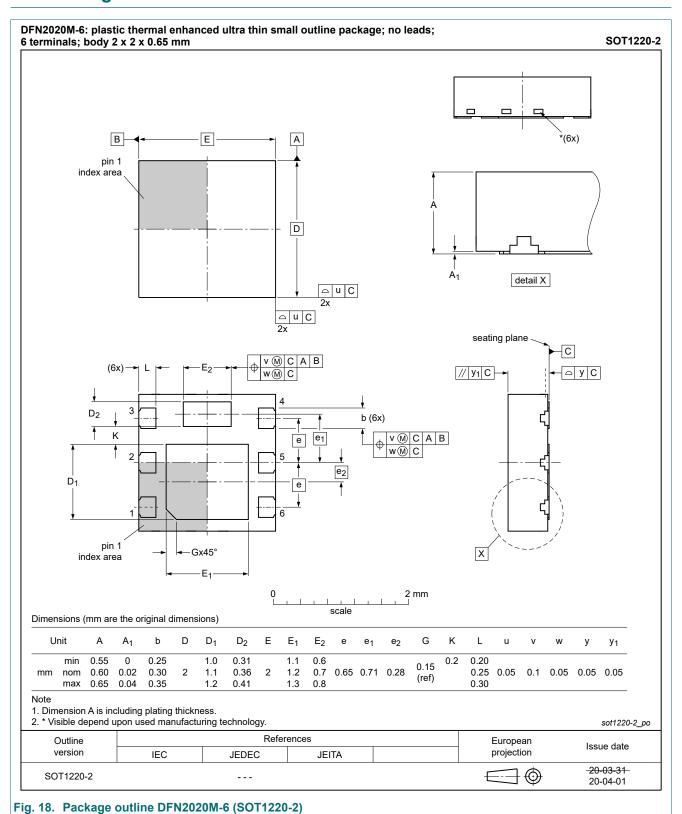
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## 11. Test information



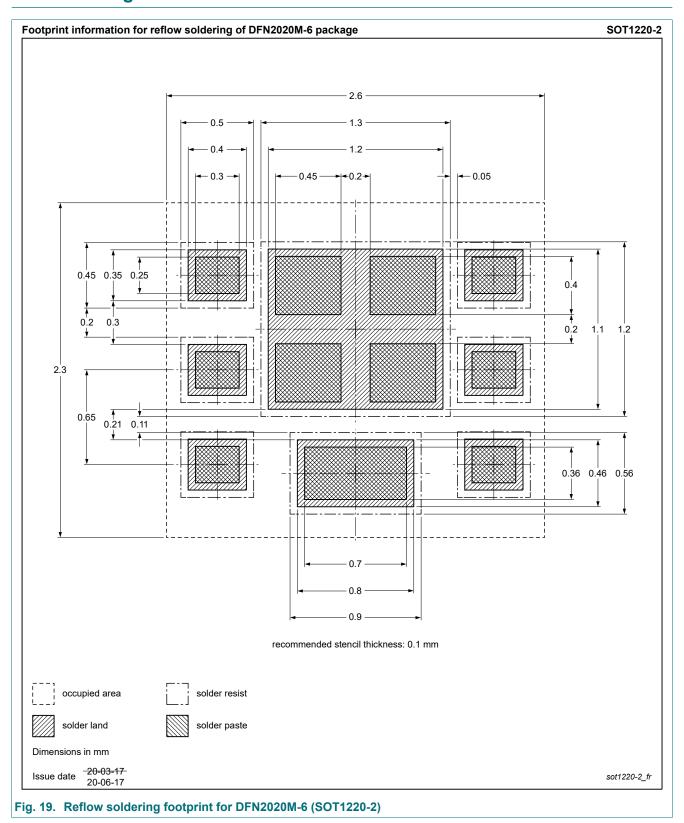
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# 12. Package outline



30 V, N-channel Trench MOSFET

## 13. Soldering



30 V, N-channel Trench MOSFET

# 14. Revision history

## Table 8. Revision history

| Data sheet ID  | Release date | Data sheet status  | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| PMPB07R3EN v.1 | 20201127     | Product data sheet | -             | -          |

### 30 V, N-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

| Document status [1][2]          | Product<br>status [3] | Definition  |
|---------------------------------|-----------------------|---|
| Objective [short]<br>data sheet | Development           | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet  | Qualification         | This document contains data from the preliminary specification.                       |
| Product [short]<br>data sheet   | Production            | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
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